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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/044,799	01/10/2002	Jun Seo	8750-018	8382
7	590 11/21/2003	EXAMINER		
MARGER JOHNSON & McCOLLOM, P.C.			LEE, GRANVILL D	
1030 SW Morrison Street Portland, OR 97205			ART UNIT	PAPER NUMBER
,			2825	
·		DATE MAILED: 11/21/200	3	

Please find below and/or attached an Office communication concerning this application or proceeding.

		G G				
	Application No.	Applicant(s)				
	10/044,799	SEO ET AL.				
Office Action Summary	Examiner	Art Unit				
	Granvill D Lee, Jr	2825				
The MAILING DATE of this communication ap Period for Reply	ppears on the cover sheet w	ith the correspondence address				
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a rep If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status		reply be timely filed ty (30) days will be considered timely. NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).				
1) Responsive to communication(s) filed on 12.4	August 2003.					
· - ·	s action is non-final.					
3) Since this application is in condition for allowed	-					
Disposition of Claims						
 4) Claim(s) 1-14 is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) Claim(s) 1-9 is/are allowed. 6) Claim(s) 10-14 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or control of the application of the application of the application and/or claim(s) are subject to restriction and/or claim(s) are subject to restriction and/or claim(s) are subject to restriction. 	awn from consideration.					
Application Papers						
9) The specification is objected to by the Examin 10) The drawing(s) filed on is/are: a) accomposite and applicant may not request that any objection to the Replacement drawing sheet(s) including the correct and the option of the correct and the co	cepted or b) objected to e drawing(s) be held in abeya ction is required if the drawing	nce. See 37 CFR 1.85(a). g(s) is objected to. See 37 CFR 1.121(d).				
Priority under 35 U.S.C. §§ 119 and 120						
12) △ Acknowledgment is made of a claim for foreigna) △ All b) ☐ Some * c) ☐ None of: 1. △ Certified copies of the priority documents. 2. ☐ Certified copies of the priority documents. 3. ☐ Copies of the certified copies of the priority documents. * See the attached detailed Office action for a list. 13) ☐ Acknowledgment is made of a claim for domest since a specific reference was included in the first sentence of the priority documents. 13) ☐ The translation of the foreign language priority. 14) ☐ Acknowledgment is made of a claim for domest reference was included in the first sentence of the priority documents.	nts have been received. Ints have been received in a pority documents have been au (PCT Rule 17.2(a)). It of the certified copies notice priority under 35 U.S.C rest sentence of the specific rovisional application has bette priority under 35 U.S.C	Application No In received in this National Stage received. § 119(e) (to a provisional application) cation or in an Application Data Sheet. peen received. §§ 120 and/or 121 since a specific				
Attachment(s)	_					
1) Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948)		Summary (PTO-413) Paper No(s) Informal Patent Application (PTO-152)				

U.S. Patent and Trademark Office PTOL-326 (Rev. 11-03)

2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)

6) Other:

Art Unit: 2825

DETAILED ACTION

Response to Applicant's Argument

After review of applicant's amendments and comments, the examiner finds such arguments unpersuasive. Applicant's comments as to Lee et al. and Doan are well taken, however in further review of the prior art, the examiner has found that Abernathey et al. read upon applicant's claimed invention. As these are new grounds for rejection not necessitated by applicant's amended claimed invention, and they are not to be considered final rejections of the claims.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 10-12 are rejected under 35 U.S.C. 102(b) as being anticipated by Abernathey et al. (US Pat. 4,755,478).

In view of these claims, Abernathey et al. teaches a method of manufacturing a semiconductor device comprising forming a gate stack (#100) on a semiconductor substrate (#1) and forming a gate spacer (#60) on

Art Unit: 2825

sidewalls of the gate stack wherein the gate spacer includes a top portion substantially lower than the top of the gate stack (Fig. 6).

Further, in view of claim 11, Abernathey et al. includes an interlayer insulating layer (Fig. 4 #90a) over the gate stack and the gate spacer (Fig. 4).

In further view of claim 12, Abernathey et al. teaches that an oxide layer is formed before the interlayer insulating layer, forming a blanket etching stop layer over the entire structure of the gate stack and spacer (Col. 5 lines 15-25).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 13 and 14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Abernathey et al. (US Pat. 4,755,478) in view of the admitted prior art (Fig. 1-2c).

In view of these claims, Abernathey et al. teaches a method of manufacturing a semiconductor device comprising forming a gate stack on a semiconductor substrate and forming a gate spacer on sidewalls of the gate stack wherein the gate spacer includes a top portion substantially lower than the top of the gate stack. But Abernathey et al. fails to make mention of a self-aligned contact formation. However, the admitted prior art (APA) discusses a plurality of gates

Art Unit: 2825

where self-aligned contacts are formed. Namely, APA suggests that contact holes may not be aligned "precisely" (Pg. 1 lines 28-29), and that an alignment method may be needed as shown in figures 2a-2c. And since it is notoriously well know to use a planarized metal contact when making self-aligned contacts, and Abernathey et al. details a metal silicide process over drain/source region (Col. 2 lines 57-66), it therefore would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the prior art with that of Abernathey et al. to develop self aligned contacts in the regions between gates using metal that has been planarized.

Allowable Subject Matter

Claims 1-9 are allowed.

Contact Information

Any inquiry concerning this communication or earlier communications for the examiner should be directed to Granvill Lee whose telephone number is (703) 306-5865. The examiner can be normally reached on Monday thru Thursday from 7:00 am to 5:30 pm.

If attempts to reach the examiner by telephone are not successful, the examiner's supervisor, Matthew Smith can be reached on (703) 308-1323. The fax phone number for this group is (703) 872-9306.

Art Unit: 2825

99 Page 5

Any inquiry of a general nature relating to status or otherwise should be directed to the receptionist whose telephone number is 703-308-1782.

Examiner Granvill Lee Art Unit 2825

Gl 11/11/03

> MATTHEW SMITH SUPERVISORY PATENT EXAMINER

TECHNOLOGY CENTER 2800